

# WESTCODE SEMICONDUCTORS

Technical  
Publication  
**TN560C**  
Issue 1  
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## Converter Grade Capsule Thyristor Type N560C 1320 amperes average: up to 4200 volts $V_{RRM}$

### Ratings (Maximum values at 125°C T<sub>J</sub> unless stated otherwise)

RATING	CONDITIONS	SYMBOL	
Average on-state current	Half sine wave $\left\{ \begin{array}{l} 55^\circ\text{C heatsink temperature} \\ \text{(double side cooled)} \\ 85^\circ\text{C heatsink temperature} \\ \text{(single side cooled)} \end{array} \right.$	$I_{T(AV)}$	1320 A 560 A
R.M.S. on-state current	25°C heatsink temperature, double side cooled	$I_T(RMS)$	2600 A
Continuous on-state current	25°C heatsink temperature, double side cooled	$I_T$	2275 A
Peak one-cycle surge (non-repetitive) on state current	10ms duration, 60% $V_{RRM}$ re-applied	$I_{TSM(1)}$	19000 A
	10ms duration, $V_R \leq 10$ volts	$I_{TSM(2)}$	20900 A
Maximum permissible surge energy	10ms duration, $V_R \leq 10$ volts	$W_{PR(2)}$	$2.18 \times 10^5 \text{ A}^2\text{s}$
	3ms duration, $V_R \leq 10$ volts	$W_{PR}$	$1.6 \times 10^5 \text{ A}^2\text{s}$
Peak forward gate current	Anode positive with respect to cathode	$I_{FGM}$	20 A
Peak forward gate voltage	Anode positive with respect to cathode	$V_{FGM}$	22 V
Peak reverse gate voltage		$V_{RGM}$	5 V
Average gate power		$P_G$	4 W
Peak gate power	100µs. pulse width	$P_{GM}$	120 W
Rate of rise of off-state voltage	To 80% $V_{DRM}$ gate open-circuit	$dv/dt$	$\approx 200 \text{ V}/\mu\text{s}$
Rate of rise of on-state current (repetitive)	$\left\{ \begin{array}{l} \text{Gate drive 20 volts, 20 ohms with } t_r \leq 1\mu\text{s.} \\ \text{Anode voltage } \leq 80\% V_{DRM} \end{array} \right.$	$di/dt(1)$	50 A/µs
Rate of rise of on-state current (non-repetitive)		$di/dt(2)$	100 A/µs
Operating temperature range		$T_{ns}$	-40 + 125°C
Storage temperature range		$T_{stg}$	-40 + 150°C

### Characteristics (Maximum values at 125°C T<sub>J</sub> unless stated otherwise)

CHARACTERISTIC	CONDITIONS	SYMBOL	
Peak on-state voltage	At 3220 A, $I_{TM}$	$V_{TM}$	2.63 V
Forward conduction threshold voltage		$V_O$	1.15 V
Forward conduction slope resistance		$r$	0.46 mΩ
Repetitive peak off-state current	At $V_{DRM}$	$I_{DRM}$	150 mA
Repetitive peak reverse current	At $V_{RRM}$	$I_{RRM}$	150 mA
Maximum gate current required to fire all devices	$\left\{ \begin{array}{l} V_A = 6 \text{ V, } I_A = 2 \text{ A at } 25^\circ\text{C T}_J \end{array} \right.$	$I_{GT}$	300 mA
Maximum gate voltage required to fire all devices		$V_{GT}$	3 V
Maximum holding current		$I_H$	1 A
Maximum gate voltage which will not trigger any device		$V_{GD}$	0.25 V
Thermal resistance, junction to heatsink, for a device with a maximum forward volt drop characteristic	Double side cooled	$R_{th(j-hs)}$	0.02°C/W
	Single side cooled		0.04°C/W

VOLTAGE CODE		H36	H38	H40	H42				
Repetitive peak voltages	$V_{RRM}$ $V_{DRM}$								
Non-repetitive peak off-state voltage	$V_{DSM}$	3600	3600	4000	4200				
Non-repetitive peak reverse blocking voltage	$V_{RSM}$	3700	3900	4100	4300				

### Ordering Information (Please quote device code as explained below - 8 digits)

N 5 6 0 C	● ● ●	
	Voltage code (see ratings)	Typical code: N560CH40 = 4000 $V_{RRM}$ 4000 $V_{DRM}$ 200 V/µs $dv/dt$ to 80% $V_{DRM}$

\* Other values of  $dv/dt$  may be available.

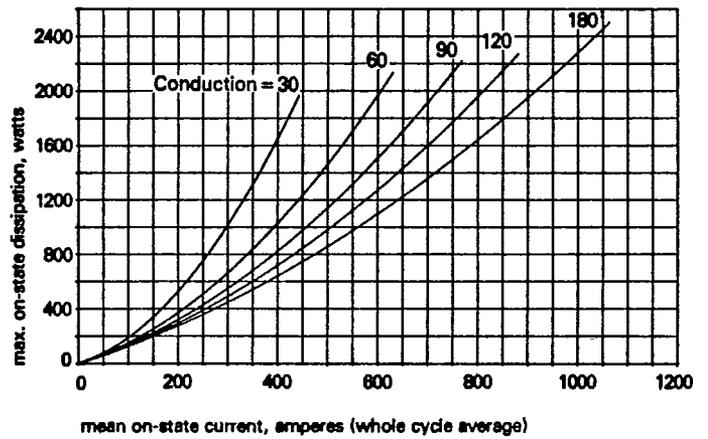
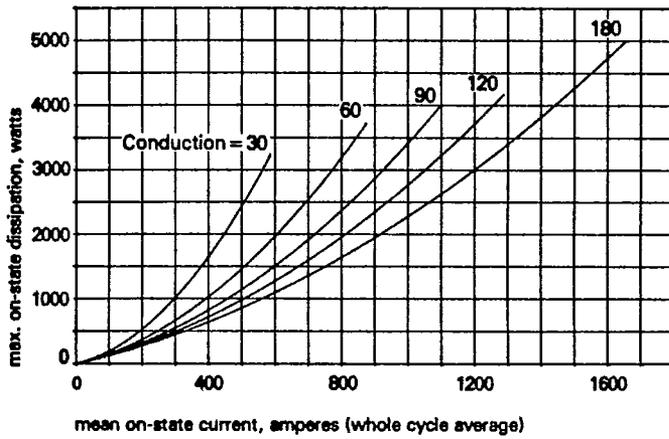
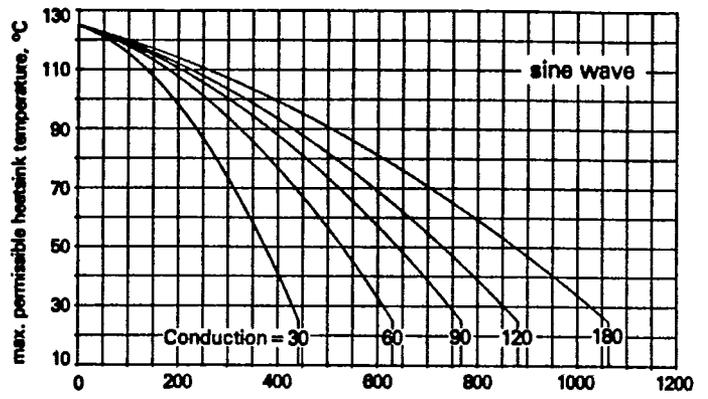
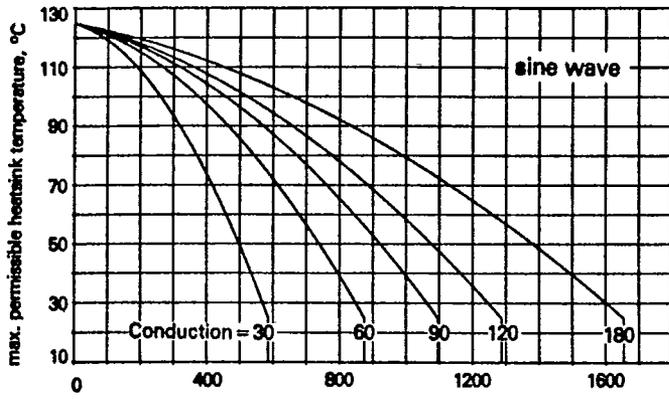


Figure 1 Dissipation and heatsink temperature v. current (Double side cooled)

Figure 2 Dissipation and heatsink temperature v. current (Single side cooled)

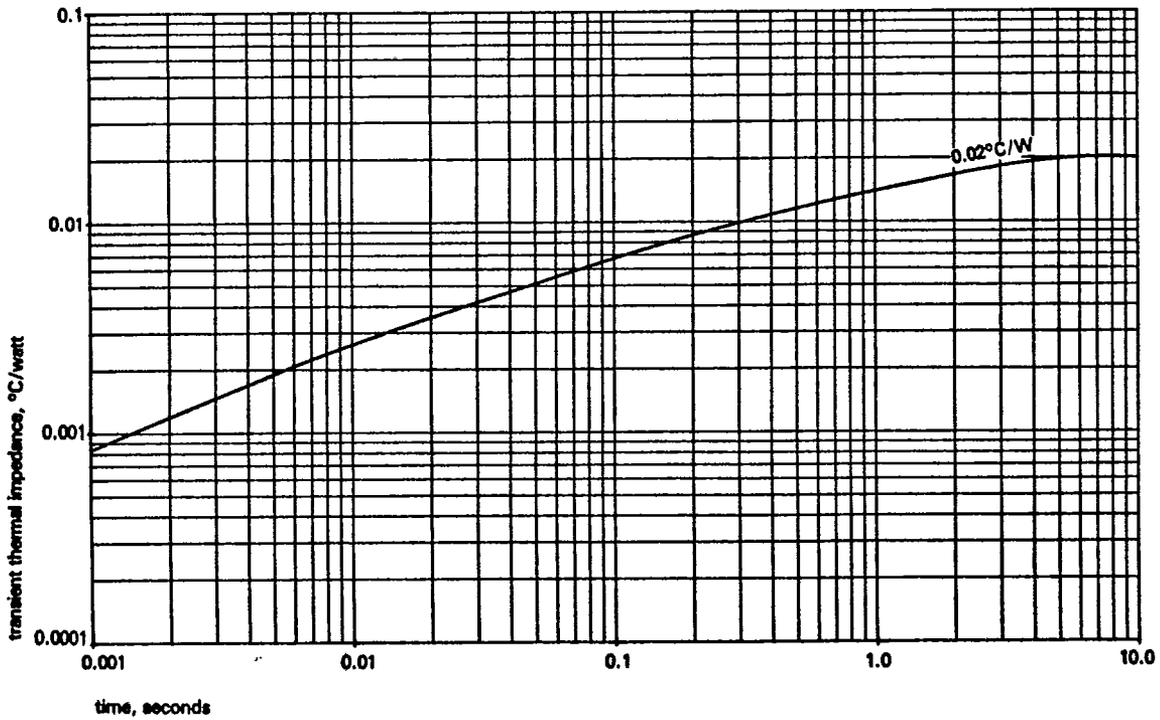


Figure 3 Junction to heatsink thermal impedance

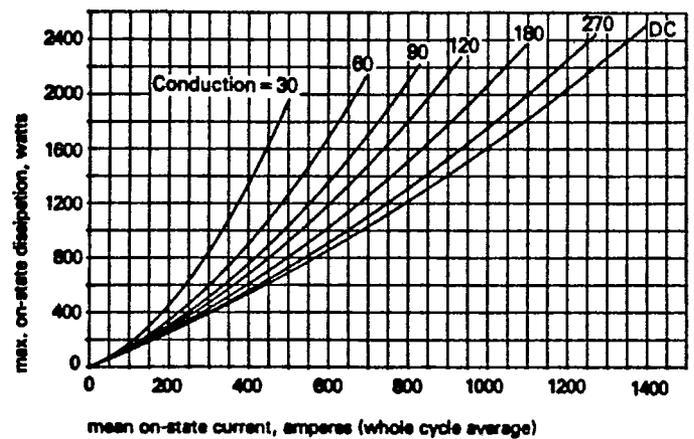
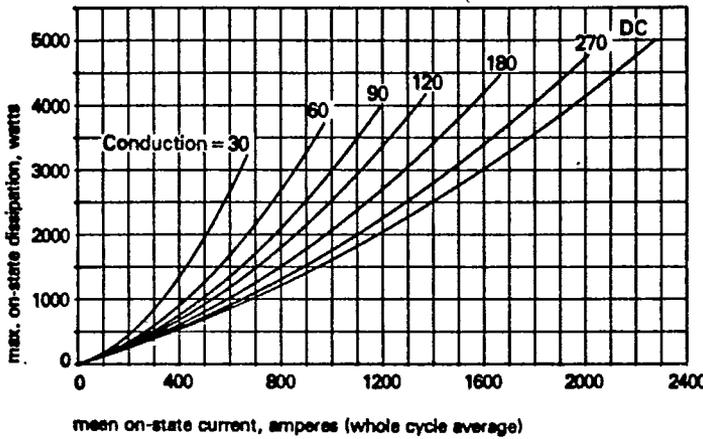
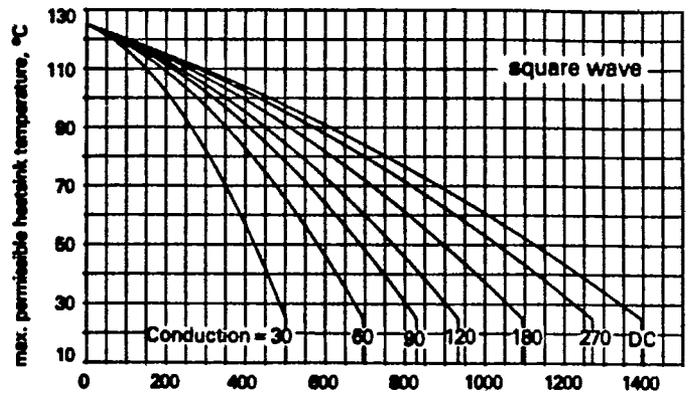
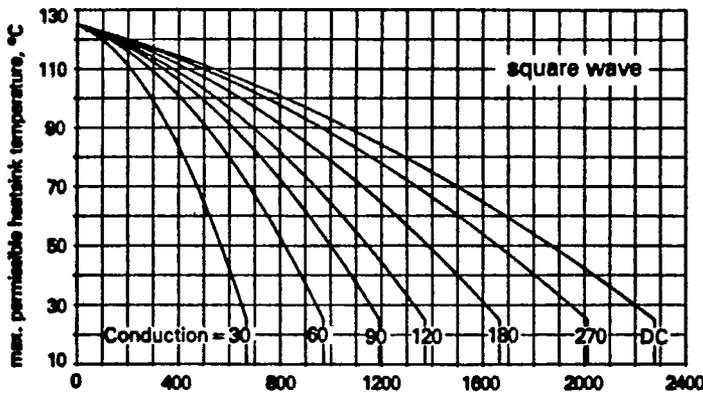


Figure 4 Dissipation and heatsink temperature v. current (Double side cooled)

Figure 5 Dissipation and heatsink temperature v. current (Single side cooled)

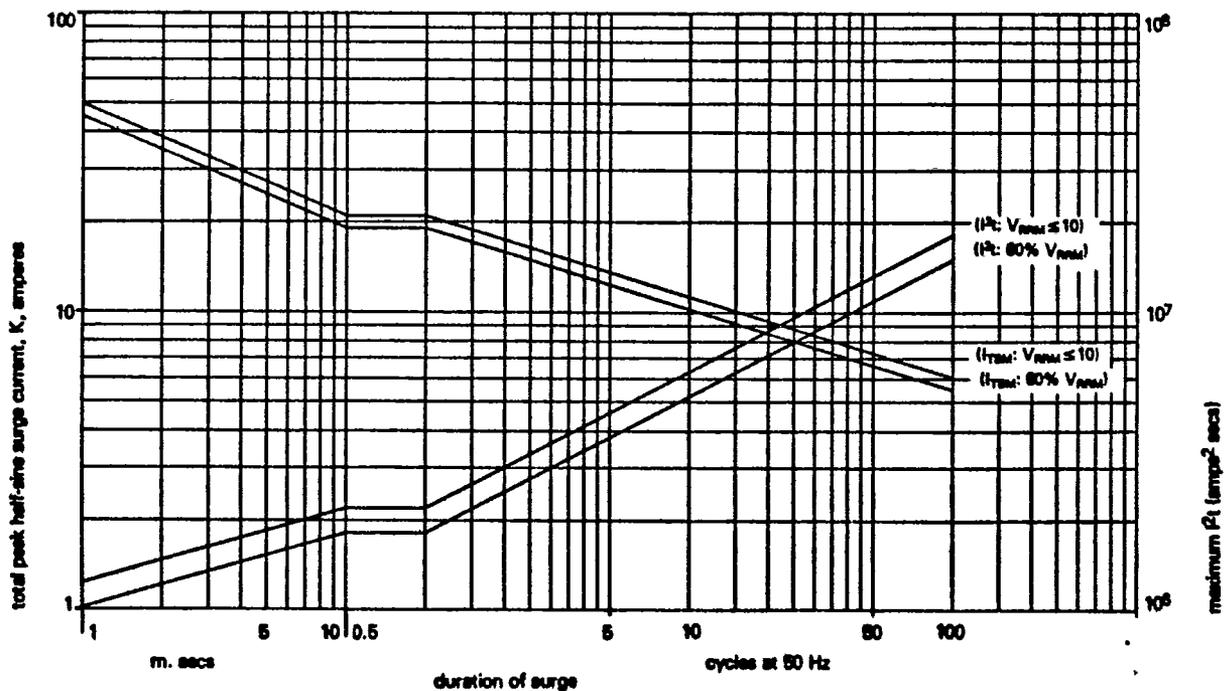


Figure 6 Max. non-repetitive surge current at initial junction temperature 125°C.

(gate may temporarily lose control of firing angle)

Note: This rating must not be interpreted as an intermittent rating

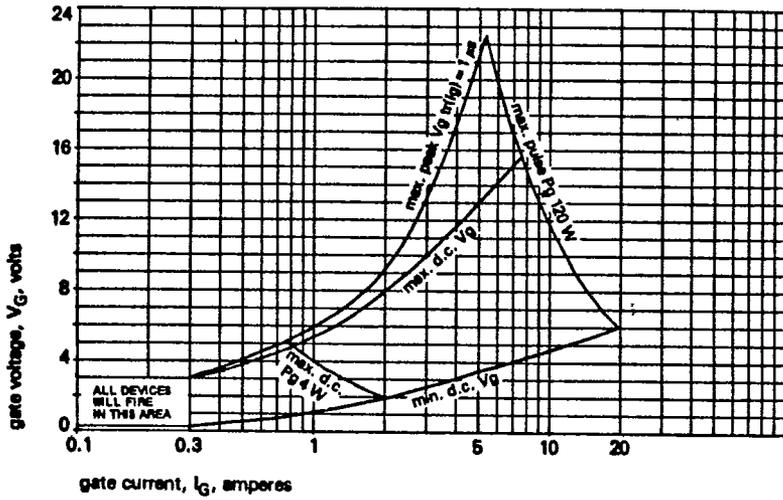


Figure 7 Gate characteristics at 25°C junction temperature

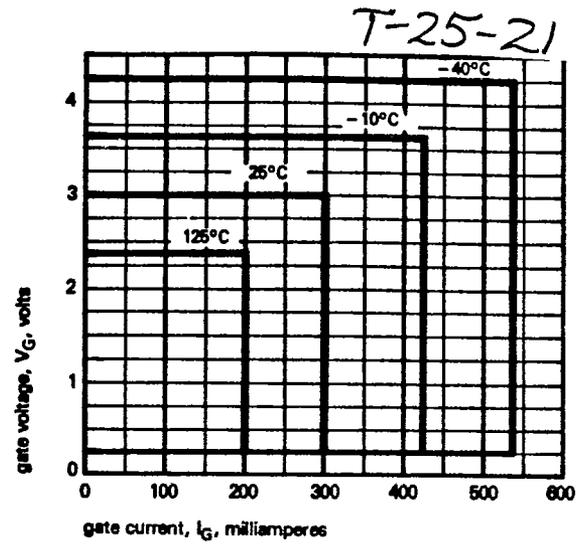


Figure 8 Gate triggering characteristics  
Trigger points of all thyristors lie within the areas shown

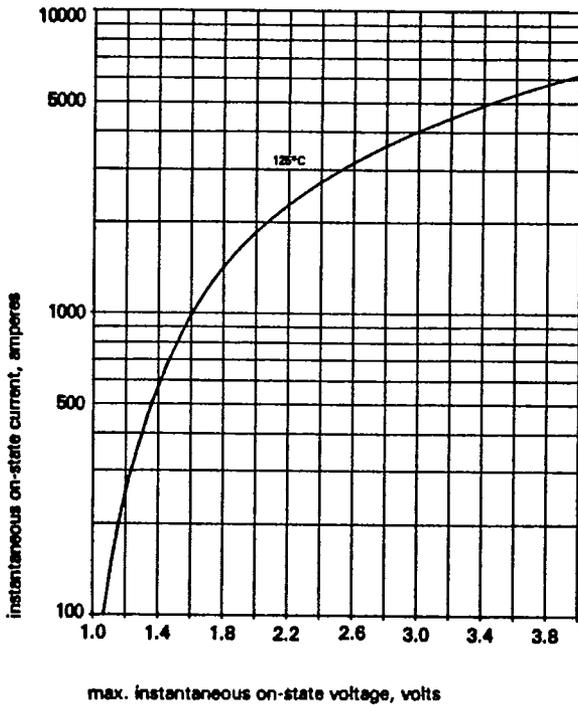
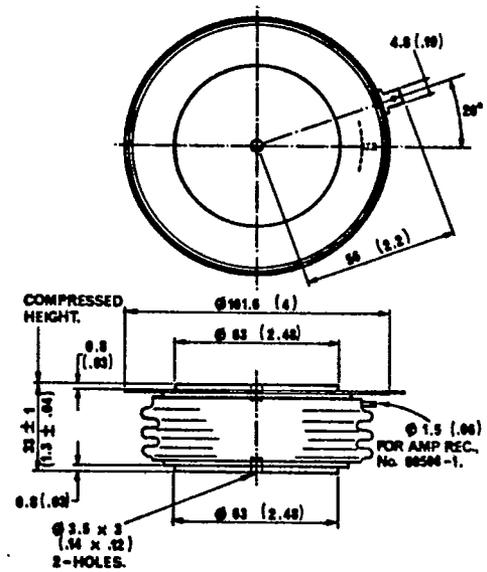


Figure 9 Limit on-state characteristic at 125°C



Dimensions in mm (inches)  
Mounting force: 2700-3400 Kg  
Weight: 1000 grams

In the interest of product improvement, Westcode reserves the right to change specifications at any time without notice.

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